30-F2126TA075M7-L288F74
datasheet

***flow*PACK 2** | **1200 V / 75 A**

Topology features

- Kelvin Emitter for improved switching performance
- Open Emitter configuration
- Temperature sensor
- 3xHalf Bridge
- Tandem inverter diode

Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current
- Switching optimized for EMC

Housing features

- Base isolation: Al_2O_3
- Convex shaped baseplate for superior thermal contact
- Cu baseplate
- Thermo-mechanical push-and-pull force relief
- Solder pin

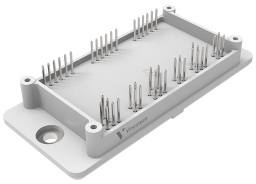
Target applications

- Servo Drives

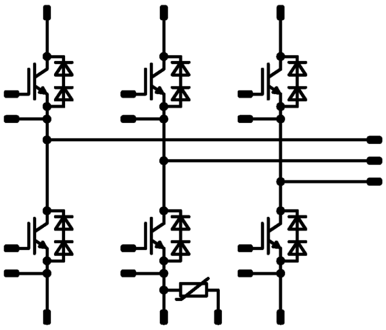
Types

- 30-F2126TA075M7-L288F74

flow 2 17 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Inverter Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	95	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	191	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			1300	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	66	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	189	W
Maximum junction temperature	T_{jmax}			175	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				>12,7	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0075	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		75	25 125 150		1,55 1,7 1,75	1,9(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			100	μA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							4		Ω
Input capacitance	C_{ies}		0	10		25		16000		pF
Output capacitance	C_{oes}		0	10		25		480		pF
Reverse transfer capacitance	C_{res}		0	10		25		190		pF
Gate charge	Q_g	V_{CC} = 600 V	0/15		75	25		570		nC
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,5		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	600	75	25 125 150		259,15 267,6 269,04		ns
Rise time	t_r	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	600	75	25 125 150		46,65 55,36 58,1		ns
Turn-off delay time	$t_{d(off)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	600	75	25 125 150		219,86 255,55 264,29		ns
Fall time	t_f	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	600	75	25 125 150		109,12 132,4 143,75		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,19 μC Q_{rFWD}=2,99 μC Q_{rFWD}=3,48 μC	±15	600	75	25 125 150		3,53 5,37 5,77		mWs
Turn-off energy (per pulse)	E_{off}		±15	600	75	25 125 150		5,52 7,4 7,89		mWs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Inverter Diode										
Static										
Forward voltage	V_F				75	25 125 150		3,36 3,11 3,04	3,84(1)	V
Reverse leakage current	I_R	V_r = 1300 V				25			3,8	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,5		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=1569 A/µs di/dt=1243 A/µs di/dt=1312 A/µs	±15	600	75	25 125 150		17,26 29,85 31,73		A
Reverse recovery time	t_{rr}					25 125 150		113,84 164,1 175,94		ns
Recovered charge	Q_r					25 125 150		1,19 2,99 3,48		µC
Reverse recovered energy	E_{rec}					25 125 150		0,464 1,12 1,31		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		574,94 433,97 460,14		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

(1) Value at chip level

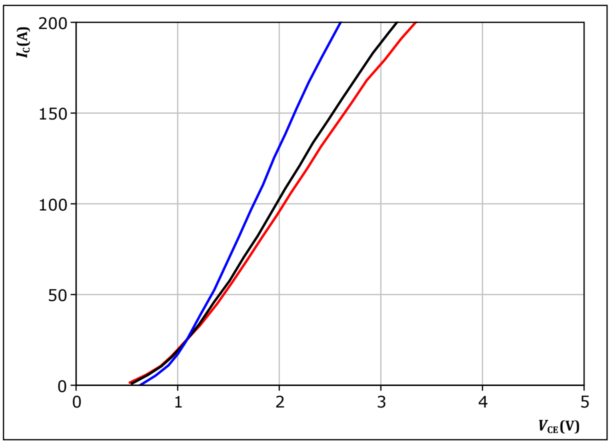
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



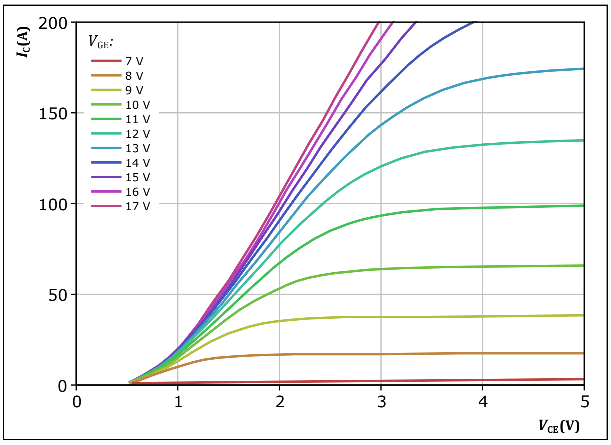
t_p =	250	µs
V_{GE} =	15	V

T_j: 25 °C, 125 °C, 150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



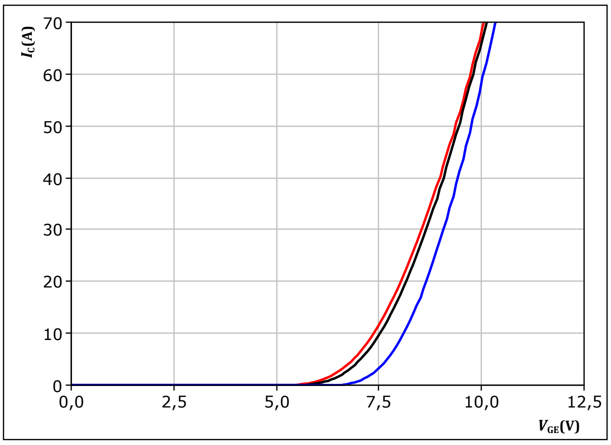
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



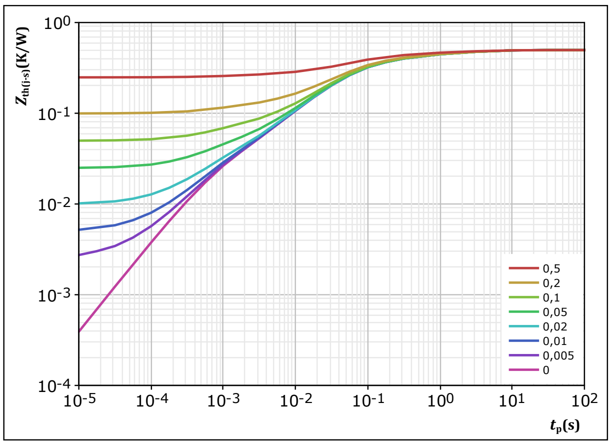
t_p =	250	µs
V_{CE} =	10	V

T_j: 25 °C, 125 °C, 150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	0,497	K/W

IGBT thermal model values

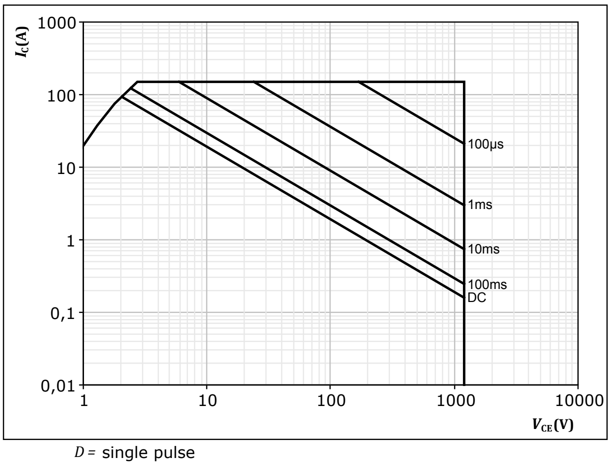
R (K/W)	τ (s)
4,16E-02	4,25E+00
5,55E-02	8,53E-01
1,25E-01	1,69E-01
2,12E-01	3,95E-02
4,29E-02	8,08E-03
2,08E-02	7,43E-04

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})

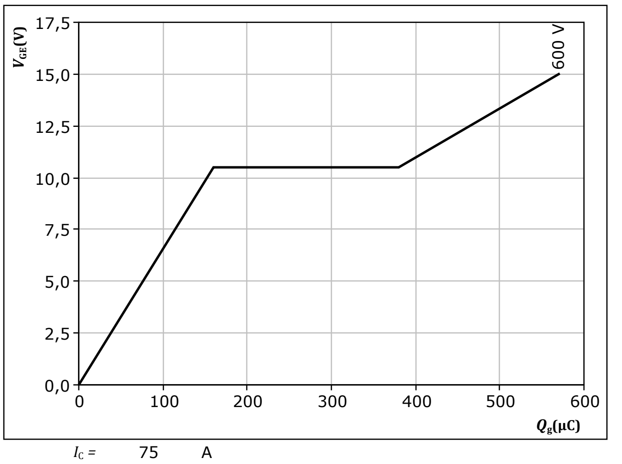


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 6. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



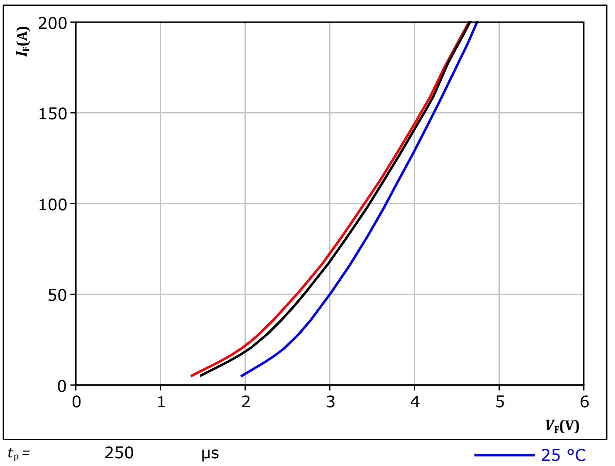
I_C = 75 A
T_j = 25 °C

Inverter Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

I_F = f(V_F)



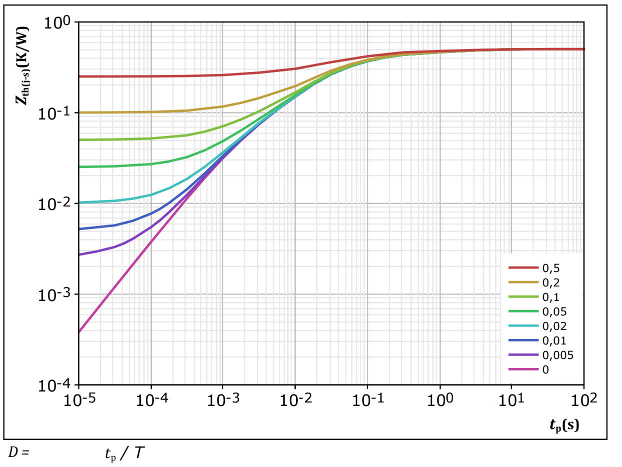
t_p = 250 μs

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,501 K/W

FWD thermal model values

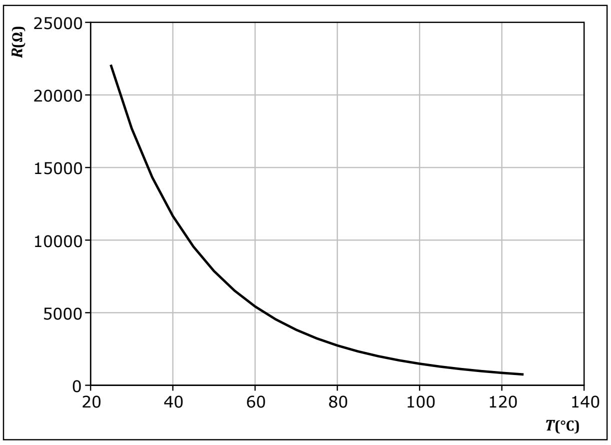
R (K/W)	τ (s)
2,98E-02	3,90E+00
5,18E-02	7,55E-01
1,94E-01	8,12E-02
1,88E-01	1,55E-02
3,77E-02	1,59E-03

Thermistor Characteristics

figure 9.	Thermistor

Typical NTC characteristic as function of temperature

R_T = f(T)

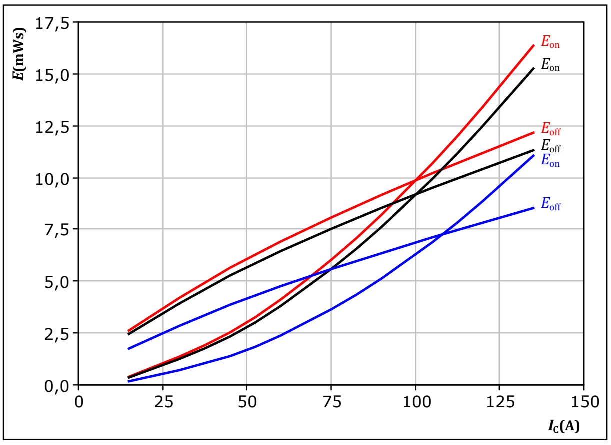


Inverter Switching Characteristics

figure 10. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



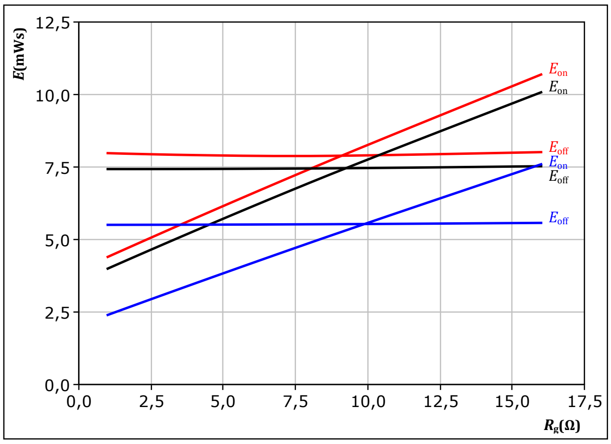
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C
R_{goff} =	4	Ω		

figure 11. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



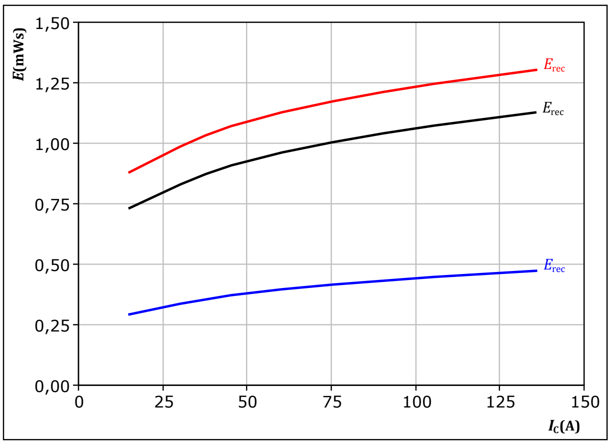
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	75	A		150 °C

figure 12. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



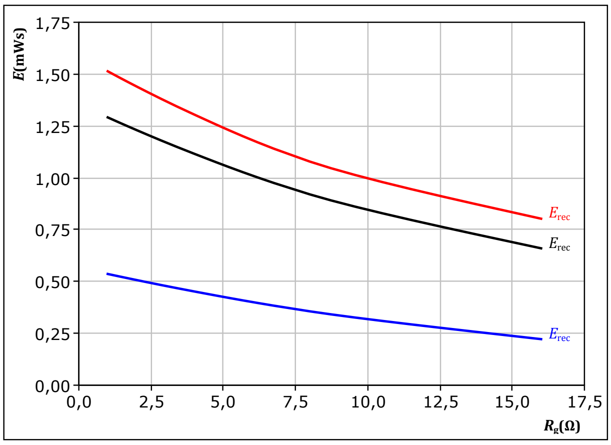
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 13. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

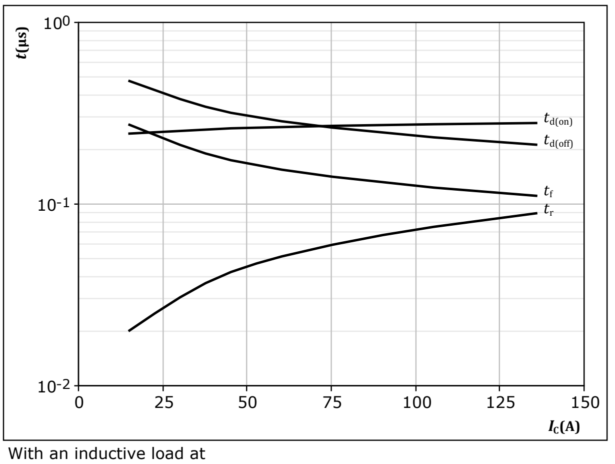
V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	75	A		150 °C

Inverter Switching Characteristics

figure 14. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



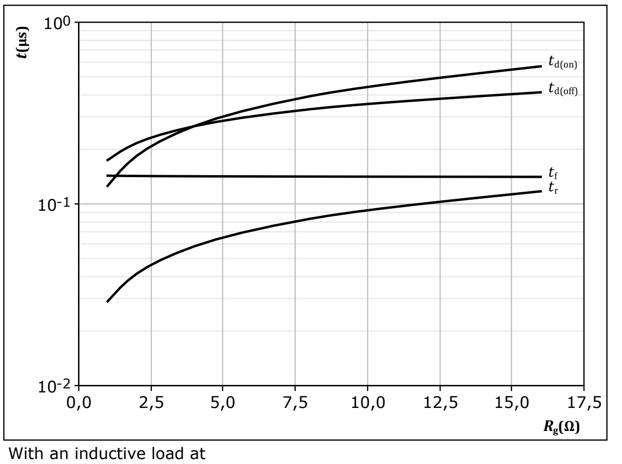
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 15. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



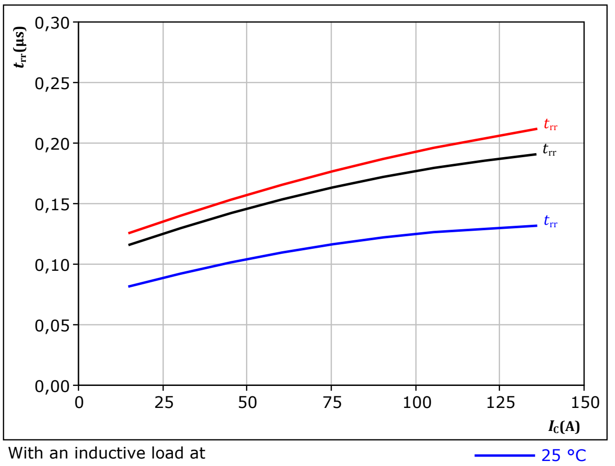
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	75	A

figure 16. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

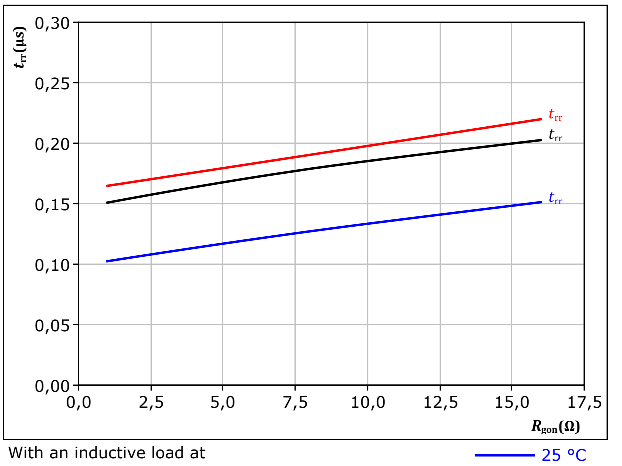
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 17. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	75	A

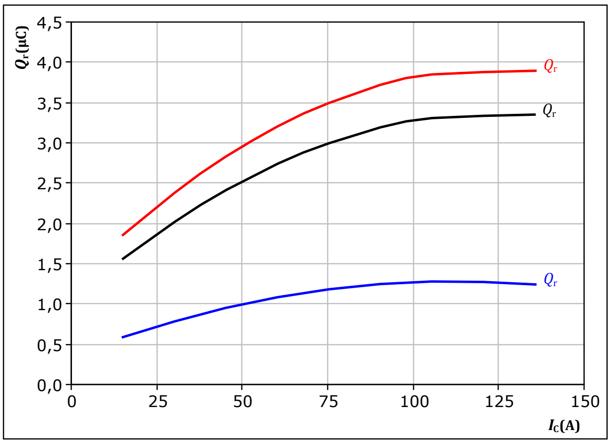
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 18. FWD

Typical recovered charge as a function of collector current

Q_r = f(I_C)



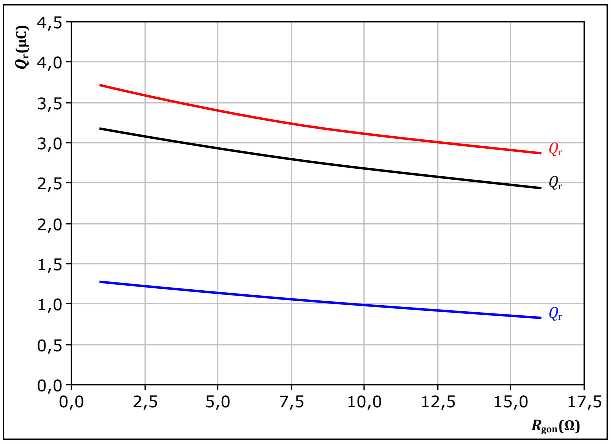
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 19. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



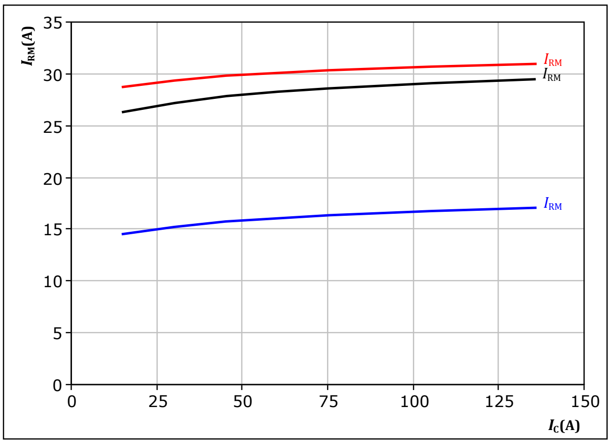
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	75	A		150 °C

figure 20. FWD

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



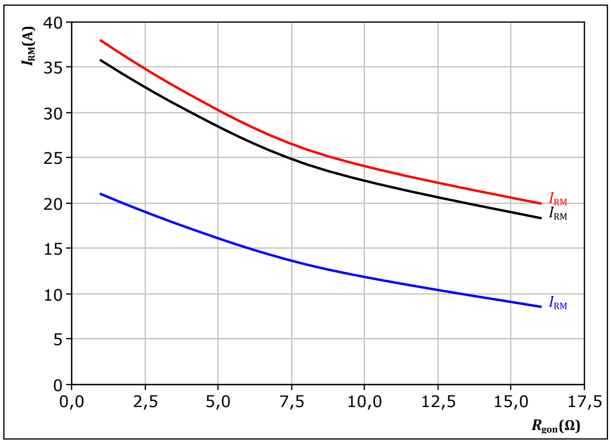
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 21. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

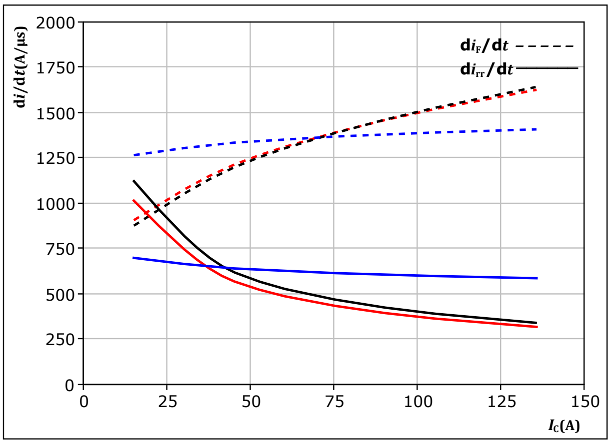
V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	75	A		150 °C

Inverter Switching Characteristics

figure 22. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



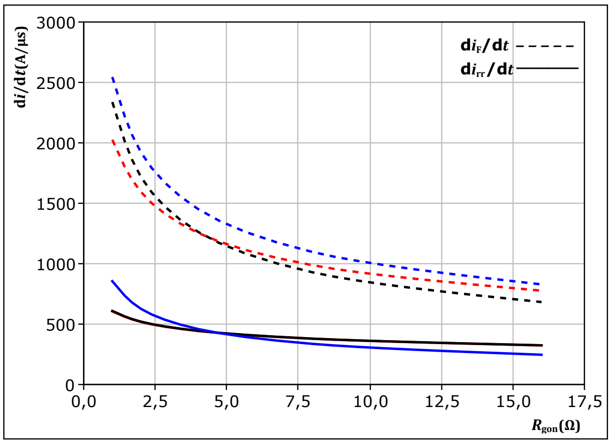
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 23. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



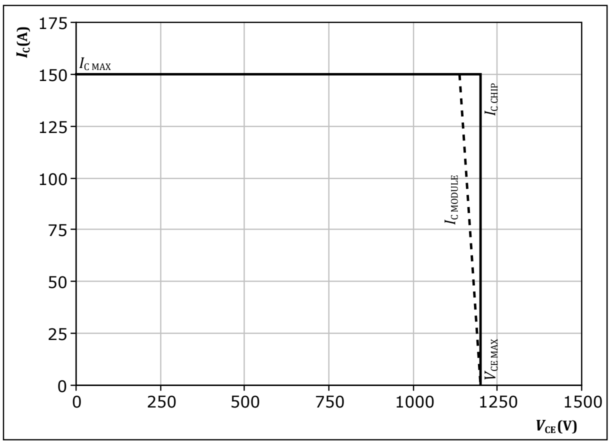
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	75	A		150 °C

figure 24. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	4	Ω
	R_{goff} =	4	Ω

Inverter Switching Definitions

figure 25. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} **= integrating time for** E_{off})

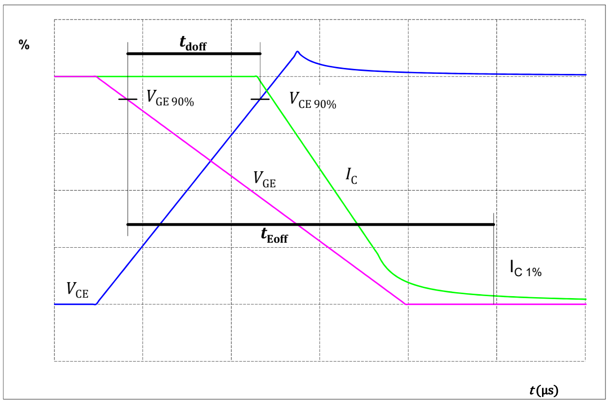


figure 26. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} **= integrating time for** E_{on})

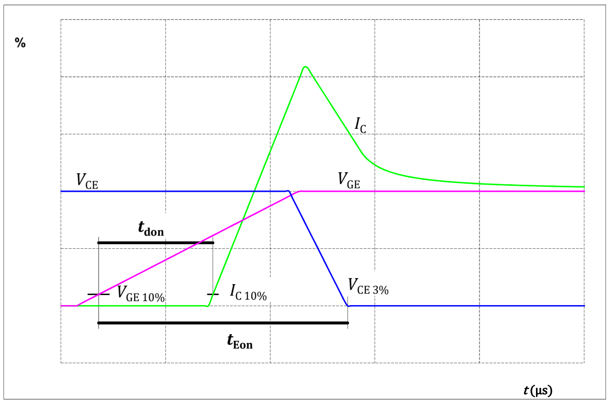


figure 27. **IGBT**

Turn-off Switching Waveforms & definition of t_f

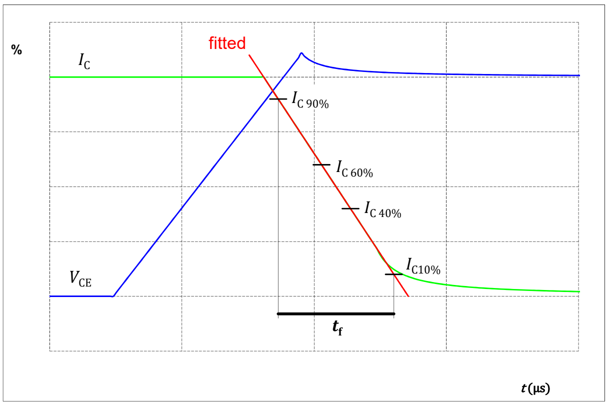
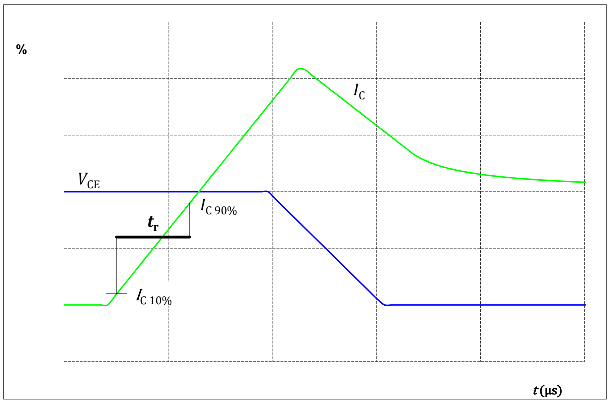


figure 28. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Inverter Switching Definitions

figure 29. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

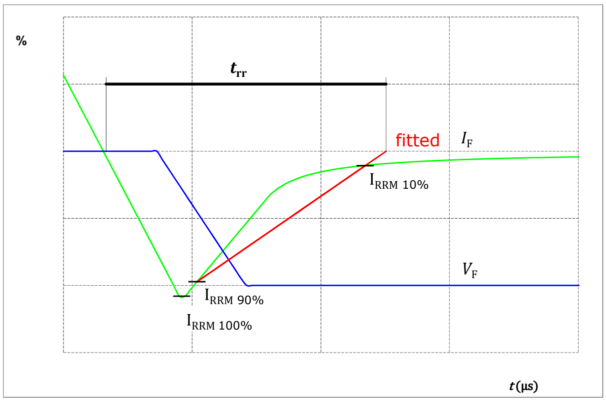
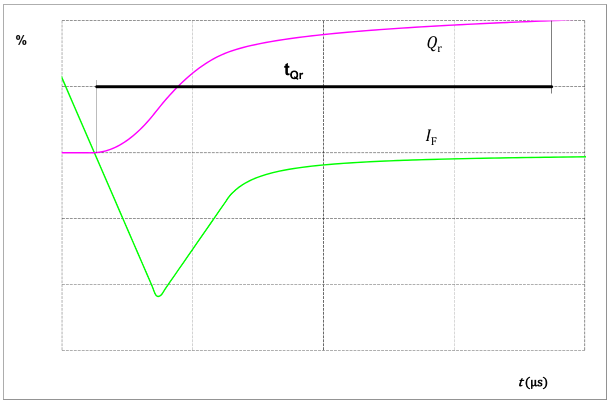


figure 30. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

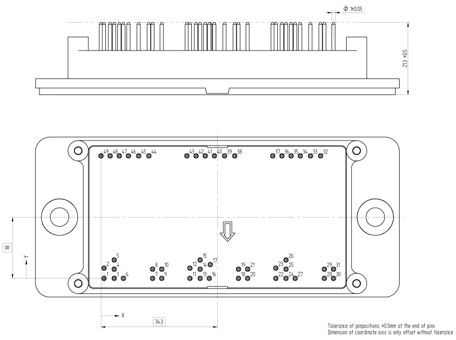
Version	Ordering Code
Without thermal paste	30-F2126TA075M7-L288F74
With thermal paste (3,4 W/mK, PSX-P7)	30-F2126TA075M7-L288F74-/3/

Marking

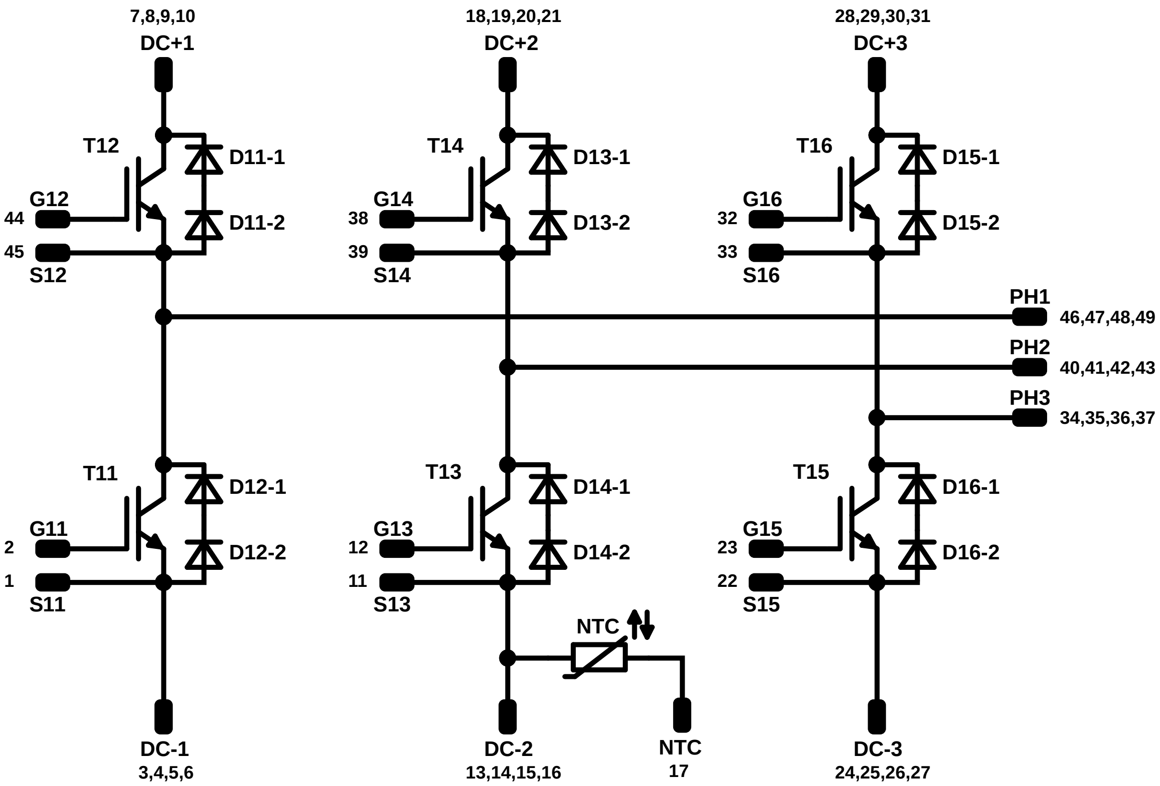
	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table [mm]							
Pin	X	Y	Function	26	54,5	5,4	DC-3
1	0,9	0	S11	27	57,2	0	DC-3
2	0,9	3	G11	28	65,8	0	DC+3
3	3,9	0	DC-1	29	65,8	2,7	DC+3
4	3,9	2,7	DC-1	30	68,5	0	DC+3
5	3,9	5,4	DC-1	31	68,5	2,7	DC+3
6	6,6	0	DC-1	32	64,7	36	G16
7	15,2	0	DC+1	33	61,7	36	S16
8	15,2	2,7	DC+1	34	58,7	36	PH3
9	17,9	0	DC+1	35	56	36	PH3
10	17,9	2,7	DC+1	36	53,3	36	PH3
11	26,2	0	S13	37	50,6	36	PH3
12	26,2	3	G13	38	39,4	36	G14
13	29,2	0	DC-2	39	36,4	36	S14
14	29,2	2,7	DC-2	40	33,4	36	PH2
15	29,2	5,4	DC-2	41	30,7	36	PH2
16	31,9	0	DC-2	42	28	36	PH2
17	32,2	4,05	NTC	43	25,3	36	PH2
18	40,5	0	DC+2	44	14,1	36	G12
19	40,5	2,7	DC+2	45	11,1	36	S12
20	43,2	0	DC+2	46	8,1	36	PH1
21	43,2	2,7	DC+2	47	5,4	36	PH1
22	51,5	0	S15	48	2,7	36	PH1
23	51,5	3	G15	49	0	36	PH1
24	54,5	0	DC-3				
25	54,5	2,7	DC-3				



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	75 A	Inverter Switch	
D11-1, D11-2, D12-1, D12-2, D13-1, D13-2, D14-1, D14-2, D15-1, D15-2, D16-1, D16-2	FWD	1300 V	75 A	Inverter Diode	
NTC	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 36	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 2 packages see vincotech.com website.

Package data
Package data for *flow* 2 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
30-F2126TA075M7-L288F74-D2-14	27 Apr. 2023	Change NTC	